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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

HIRASE, Masaki et al.

Group Art Unit: 2812

Serial No.: 09/908,941

Examiner: Jennifer M. Kennedy

Filed: July 20, 2001

P.T.O. Confirmation No.: 1043

For. SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME

REQUEST FOR RECONSIDERATION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Date: October 7, 2004

Sir:

Reconsideration of the rejections contained in the Office Action dated July 7, 2004, in view of the following detailed comments is respectfully requested.

In the Office Action, claims 3-4 were rejected under 35 USC § 103(a) as being unpatentable over the patent to Zhang et al in view of the patent to Krivokapic et al. In making this rejection, it was asserted as before that the cited Zhang et al patent teaches the method as claimed except for depositing the oxide insulation in the trenches by performing HDPCVD. The Krivokapic et al patent was then asserted to teach forming an insulating oxide layer in a trench using HDPCVD. It was concluded that it would be obvious to use HDPCVD in the method of the Zhang et al patent since the Krivokapic et al patent teaches HDPCVD is self-planarizing and thus facilitates subsequent production